AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently Amended) A method for manufacturing a semiconductor laser device, comprising the steps of:

forming electrode patterns arranged in a plurality of rows extending in a first direction on an upper surface of a semiconductor wafer having at least a light emission layer, the electrode patterns having opposed two edges extending in the first direction;

cutting the resultant semiconductor wafer for predetermined width to yield a plurality of semiconductor bars; and

sectioning the semiconductor bars in desired sizes to form semiconductor laser devices each having a pair of cleavage surfaces, the surfaces being parallel to a second direction and distant from each other by a resonator length,

wherein the formed electrode patterns are continuous with each other in the first direction, each electrode pattern including a series of markers having a periodical pattern which is continuous one marker to the next in the first direction, the markers being formed on one or both of the edges of the electrode patterns, and a minimum unit of the periodical pattern has an overall length in the first direction equal to L/n and not greater than the resonator length, wherein L is the resonator length and n is a positive real number not smaller than one, the first direction being a direction along the resonator length, the second direction being perpendicular to the first direction and each laser device being cut or sectioned to have a length which is an integral multiple of the length of a marker, and wherein a shape of the marker is asymmetric with respect to a hypothetical line of the electrode pattern piece extending in a chip-width direction bisectioning the overall length of the marker, and wherein each of the markers has corners at both ends in the first direction and adjacent markers point-contact with each other at the corners of their ends.

2-4 (cancelled)

5. (Currently Amended) A semiconductor laser device, comprising:

a semiconductor layer portion including at least a light emission layer and a pair of cleavage surfaces the surfaces being parallel and distant from each other by a resonator length; and

an electrode pattern piece formed on an upper surface of the semiconductor layer portion, the electrode pattern piece having opposed two first edges extending in a first direction and opposed two second edges extending in a second direction along the pair of cleavage surfaces,

wherein the two second edges come in contact with the pair of cleavage surfaces, each electrode pattern piece including a series of markers having a periodical pattern formed on one or both of the first edges, a minimum unit of the periodical pattern having an overall length in the resonator-length direction equal to L/n and not greater than a resonator length, wherein L is the resonator length and n is a positive real number not smaller than one, the first direction being a direction along the resonator length, wherein the markers can be used to form laser chips of different resonator lengths, and wherein a shape of the marker is asymmetric with respect to a hypothetical line of the electrode pattern piece extending in a chip-width direction bisectioning the overall length of the marker, and wherein each of the markers has corners at both ends in the first direction and adjacent markers point-contact with each other at the corners of their ends.

6-9 (cancelled)

10. (Previously presented) The device of claim 5, wherein the marker is set so that the ratio of its overall length in the resonator-length direction to its maximum length in the laser chip-width direction is 1:5 to 5:1.

11. (previously presented) The method of claim 1, wherein the semiconductor wafer is cut in predetermined widths to yield a plurality of semiconductor bars extending in the resonator-length direction, and the plurality of semiconductor bars are cut in predetermined resonator lengths.

12. (previously presented) The method of claim 11, wherein one of the semiconductor bars is cut in different resonator lengths to yield a plurality of different semiconductor laser devices.

13. (previously presented) The method of claim 11, wherein one of the semiconductor bars is cut in integral multiple lengths of the overall length of the marker.

14. (previously presented) The device of claim 5, wherein the series of markers are shaped like teeth of a saw.

15. (Currently amended) The device of claim 5, wherein one of the markers is formed in a shape of right triangle, ~~equilateral triangle,~~ or isosceles triangle~~, semicircle or semiellipse~~.